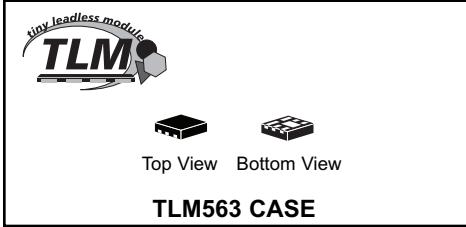




CTLDM8120-M563

**SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**



Central™ Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLDM8120-M563 is a high quality, enhancement-mode P-channel MOSFET packaged in a space saving 1.6 x 1.6mm TLM™ surface mount package. This device is a TLM™ equivalent of the popular CMLDM8120G, SOT-563 device, featuring enhanced thermal characteristics, a package footprint compatible with standard SOT-563 mounting pad geometries, and a height profile of only 0.4mm.

MARKING CODE: CKS

FEATURES:

- Device is **Halogen Free** by design
- High Current ($I_D=0.86A$)
- Low $r_{DS(ON)}$ (0.2Ω MAX @ $V_{GS}=2.5V, I_D=0.67A$)
- Logic level compatibility
- High Thermal Efficiency
- TLM563 with a package profile of 0.4mm, compatible with SOT-563 mounting geometries

APPLICATIONS:

- Load Power Switches
- DC/DC Converters
- Battery powered devices including Cell Phones, PDAs, Digital Cameras, MP3 Players, etc.

MAXIMUM RATINGS: ($T_A=25^\circ C$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Continuous Drain Current ($t \leq 5s$)
Continuous Source Current (Body Diode)
Maximum Pulsed Drain Current ($t_p=10\mu s$)
Maximum Pulsed Source Current ($t_p=10\mu s$)
Power Dissipation (Note 1)
Operating and Storage Junction Temperature
Thermal Resistance (Note 1)

SYMBOL

V_{DS} 20
 V_{GS} 8.0
 I_D 0.86
 I_D 0.95
 I_S 0.36
 I_{DM} 4.0
 I_{SM} 4.0
 P_D 500
 T_J, T_{stg} -65 to +150
 θ_{JA} 250

UNITS

V
V
A
A
A
A
A
mW
 $^\circ C$
 $^\circ C/W$

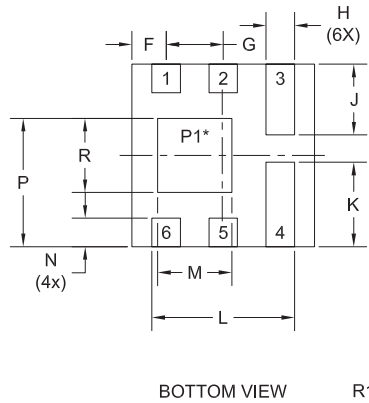
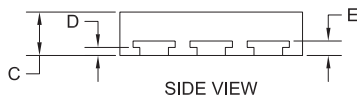
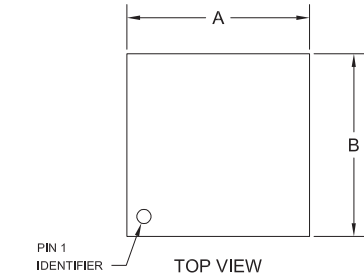
ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=8.0V, V_{DS}=0$		1.0	50	nA
I_{DSS}	$V_{DS}=20V, V_{GS}=0$		5.0	500	nA
BV_{DSS}	$V_{GS}=0, I_D=250\mu A$	20	24		V
$V_{GS(th)}$	$V_{DS}=10V, I_D=250\mu A$	0.45	0.76	1.0	V
V_{SD}	$V_{GS}=0, I_S=360mA$			0.9	V
$r_{DS(ON)}$	$V_{GS}=4.5V, I_D=950mA$		0.085	0.150	Ω
$r_{DS(ON)}$	$V_{GS}=4.5V, I_D=770mA$		0.085	0.142	Ω
$r_{DS(ON)}$	$V_{GS}=2.5V, I_D=670mA$		0.13	0.20	Ω
$r_{DS(ON)}$	$V_{GS}=1.8V, I_D=200mA$		0.19	0.24	Ω
g_{fs}	$V_{DS}=10V, I_D=810mA$	2.0			S
C_{rss}	$V_{DS}=16V, V_{GS}=0, f=1.0MHz$		80		pF
C_{iss}	$V_{DS}=16V, V_{GS}=0, f=1.0MHz$		200		pF
C_{oss}	$V_{DS}=16V, V_{GS}=0, f=1.0MHz$		60		pF
t_{on}	$V_{DD}=10V, V_{GS}=4.5V, I_D=950mA, R_G=6\Omega$		20		ns
t_{off}	$V_{DD}=10V, V_{GS}=4.5V, I_D=950mA, R_G=6\Omega$		25		ns

Notes: (1) Mounted on 2 inch square FR4 PCB with copper mounting pad area of 2.4mm².

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TLM563 CASE - MECHANICAL OUTLINE

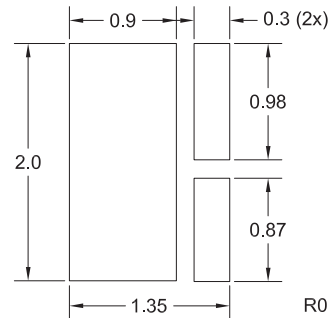


* Exposed pad P1 common to pins 1, 2, 5, and 6.

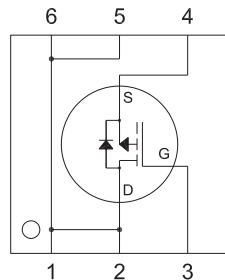
SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.062	0.064	1.57	1.63
B	0.062	0.064	1.57	1.63
C	0.014	0.017	0.36	0.43
D	0.002	0.004	0.04	0.10
E	0.004	0.006	0.10	0.16
F	0.011	0.013	0.27	0.33
G	0.019	0.021	0.47	0.53
H	0.009	0.011	0.22	0.28
J	0.023	0.026	0.59	0.65
K	0.028	0.030	0.71	0.77
L	0.048	0.050	1.22	1.28
M	0.024	0.027	0.62	0.68
N	0.009	0.011	0.22	0.28
P	0.043	0.045	1.09	1.16
R	0.024	0.027	0.62	0.68

TLM563 (REV:R1)

SUGGESTED MOUNTING PADS (Dimensions in mm)



PIN CONFIGURATION



LEAD CODE:

- 1) DRAIN
- 2) DRAIN
- 3) GATE
- 4) SOURCE
- 5) DRAIN
- 6) DRAIN

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